

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

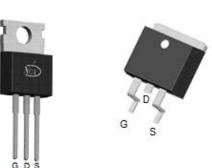
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

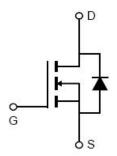
General Features

- V_{DS} =85V, I_D =260A $R_{DS(ON)}$ =2.0m Ω , typical (TO-220)@ V_{GS} =10V $R_{DS(ON)}$ =1.8m Ω , typical (TO-263)@ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

TO-220





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP023N85	NCEP023N85	TO-220	-	-	-
NCEP023N85D	NCEP023N85D	TO-263	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

TO-263

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	85	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	260	А
Drain Current-Continuous(T _C =100 ℃)	I _D (100℃)	195	А
Pulsed Drain Current	I _{DM}	1000	Α
Maximum Power Dissipation	P _D	300	W
Derating factor		2	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	2880	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^{\circ}$



NCEP023N85, NCEP023N85D

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	R _{eJC}	0.5	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	R _{0JA}	50	°C/W

Electrical Characteristics (T_C=25°C unless otherwise noted)

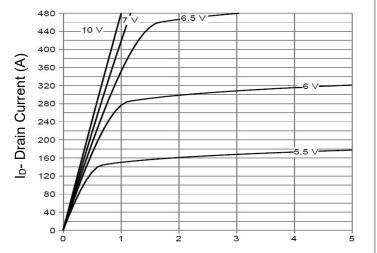
Parameter	Symbol Condition		Min	Тур	Max	Unit	
Off Characteristics				'			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA		85		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V,V _{GS}	_S =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V _{GS} =±20V,V _D	s=0V	-	-	±100	nA
On Characteristics (Note 3)				'			
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =2	50µA	2.0	3.0	4.0	V
Dunin Course On Otata Basistana	Б	\/ 40\/ I 400A	TO-220	-	2.0	2.3	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =130A	TO-263		1.8	2.3	mΩ
Gate resistance	R _G			1	-	4	Ω
Forward Transconductance	g FS	V _{DS} =5V,I _D =130A			200	-	S
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	V _{DS} =40V,V _{GS} =0V, F=1.0MHz		-	14500	-	PF
Output Capacitance	Coss			-	2100	-	PF
Reverse Transfer Capacitance	C _{rss}			-	105	-	PF
Switching Characteristics (Note 4)	,			-			
Turn-on Delay Time	t _{d(on)}			-	41	-	nS
Turn-on Rise Time	t _r	V_{DD} =40V, I_{D} =130A V_{GS} =10V, R_{G} =1.6 Ω		-	37	-	nS
Turn-Off Delay Time	t _{d(off)}			-	103	-	nS
Turn-Off Fall Time	t _f			-	38	-	nS
Total Gate Charge	Qg)/ 40)/I	1004	-	240	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =40V,I _D =130A, V _{GS} =10V		-	61		nC
Gate-Drain Charge	Q _{gd}			-	72		nC
Drain-Source Diode Characteristics				•	•		
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =1	30A	-		1.2	V
Diode Forward Current	Is			-	-	260	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =	: 130A	-	106	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/μs ^(Note3)		-	309	-	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. The value of R_{BJA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on R _{BJA} and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=40V,VG=10V,L=0.5mH,Rg=25 Ω

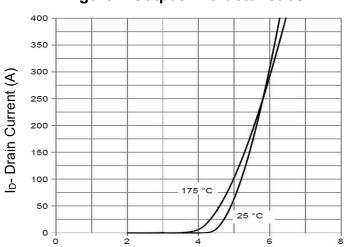


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

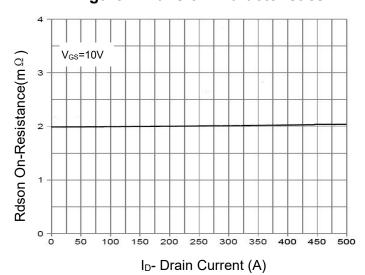
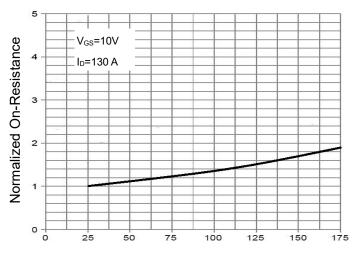


Figure 3 Rdson- Drain Current



T_J-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature

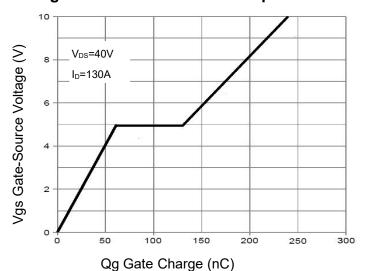
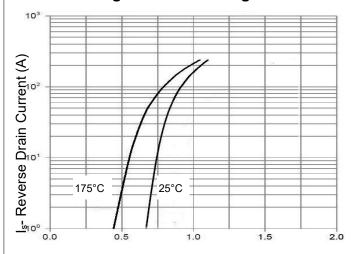


Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



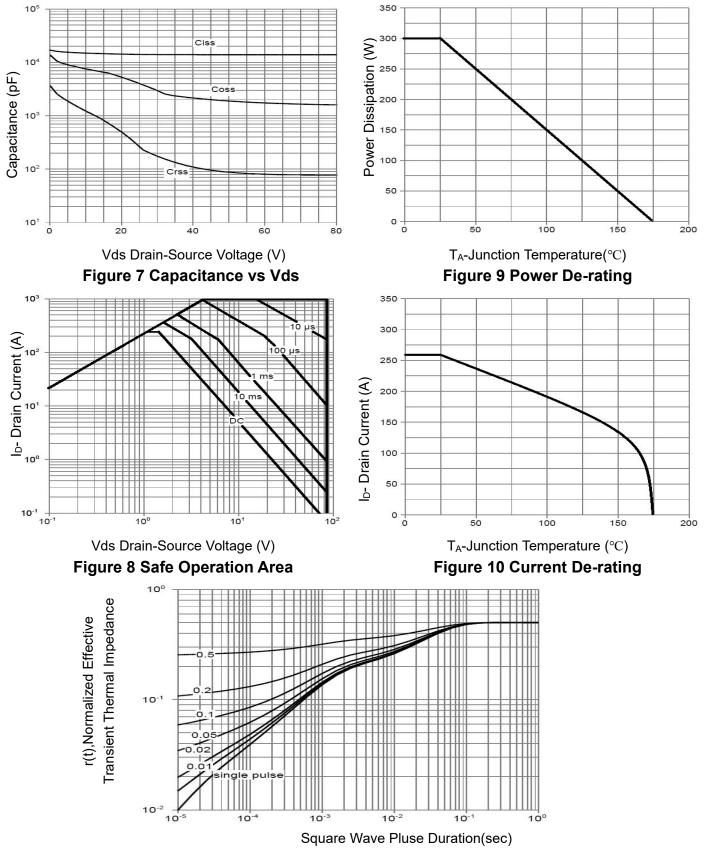
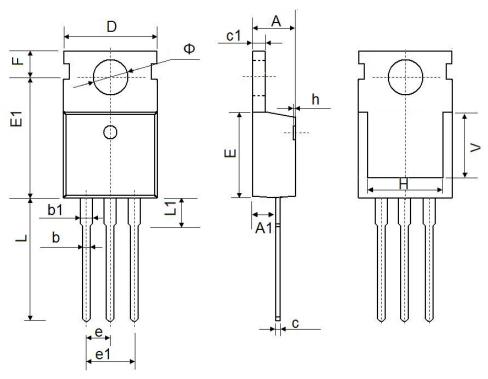


Figure 11 Normalized Maximum Transient Thermal Impedance



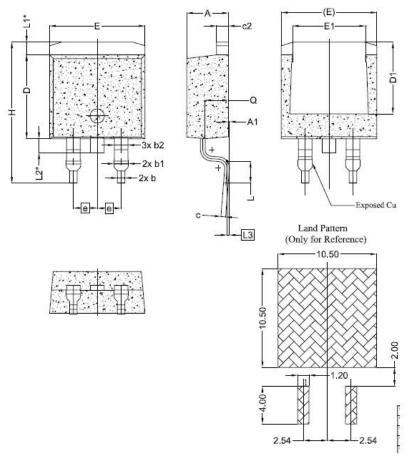
TO-220-3L Package Information



Comple al	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100	TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900	REF.	0.276	REF.	
Ф	3.400	3.800	0.134	0.150	



TO-263-2L Package Information



SYMBOL	DIMENSIONS			
	MIN.	NOM.	MAX.	
Α	4.24	4.44	4.64	
A1	0.00	0.10	0.25	
b	0,70	0.80	0.90	
b1	1.20	1,55	1.75	
b2	1,20	1,45	1,70	
С	0.40	0.50	0.60	
c2	1,15	1,27	1,40	
D	8.82	8.92	9.02	
D1	6.86	7.65		
E	9.96	10,16	10,36	
E1	6.89	7.77	7.89	
е	2.54 BSC			
н	14,61	15,00	15,88	
L	1.78	2.32	2.79	
L1	1.36 REF. 1.50 REF. 0.25 BSC			
L2				
L3				
Q	2.30	2.48	2,70	

NCEP023N85, NCEP023N85D

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